Seong Keun Kim

List of Publications by Year
in descending order

159 papers	5,220 citations	76196 40 h-index	102304 66 g-index
159 all docs	159 docs citations	159 times ranked	6076 citing authors

#	Article	IF	Citations
1	High dielectric constant TiO2 thin films on a Ru electrode grown at 250â€‰Â°C by atomic-layer deposition. Applied Physics Letters, 2004, 85, 4112-4114.	1.5	305
2	Alâ€Doped TiO₂ Films with Ultralow Leakage Currents for Next Generation DRAM Capacitors. Advanced Materials, 2008, 20, 1429-1435.	11.1	281
3	First-principles study of point defects in rutileTiO2âˆ’x. Physical Review B, 2006, 73, .	1.1	205
4	Capacitors with an Equivalent Oxide Thickness of <0.5 nm for Nanoscale Electronic Semiconductor Memory. Advanced Functional Materials, 2010, 20, 2989-3003.	7.8	189
5	Low Temperature (<100Â°C) Deposition of Aluminum Oxide Thin Films by ALD with O[sub 3] as Oxidant. Journal of the Electrochemical Society, 2006, 153, F69.	1.3	144
6	Wafer-scale growth of MoS₂thin films by atomic layer deposition. Nanoscale, 2016, 8, 10792-10798.	2.8	139
7	Comparison between ZnO films grown by atomic layer deposition using H2O or O3 as oxidant. Thin Solid Films, 2005, 478, 103-108.	0.8	136
8	Giant electrode effect on tunnelling electroresistance in ferroelectric tunnel junctions. Nature Communications, 2014, 5, 5414.	5.8	123
9	Atomic Layer Deposition of SrTiO₃ Thin Films with Highly Enhanced Growth Rate for Ultrahigh Density Capacitors. Chemistry of Materials, 2011, 23, 2227-2236.	3.2	112
10	Atomic Layer Deposition of Ru Thin Films Using 2,4-(Dimethylpentadienyl)(ethylcyclopentadienyl)Ru by a Liquid Injection System. Journal of the Electrochemical Society, 2007, 154, D95.	1.3	88
11	Future of dynamic random-access memory as main memory. MRS Bulletin, 2018, 43, 334-339.	1.7	88
12	Fabrication of high-performance p-type thin film transistors using atomic-layer-deposited SnO films. Journal of Materials Chemistry C, 2017, 5, 3139-3145.	2.7	81
13	Interfacial control of oxygen vacancy doping and electrical conduction in thin film oxide heterostructures. Nature Communications, 2016, 7, 11892.	5.8	77
14	Growth of p-Type Tin(II) Monoxide Thin Films by Atomic Layer Deposition from Bis(1-dimethylamino-2-methyl-2propoxy)tin and H₂O. Chemistry of Materials, 2014, 26, 6088-6091.	3.2	76
15	Investigation on the Growth Initiation of Ru Thin Films by Atomic Layer Deposition. Chemistry of Materials, 2010, 22, 2850-2856.	3.2	74
16	Growth Behavior of Al-Doped TiO₂ Thin Films by Atomic Layer Deposition. Chemistry of Materials, 2008, 20, 3723-3727.	3.2	69
17	Atomic Layer Deposition of SrTiO₃ Films with Cyclopentadienyl-Based Precursors for Metalâ€“Insulatorâ€“Metal Capacitors. Chemistry of Materials, 2013, 25, 953-961.	3.2	69
18	Atomic-layer-deposited Al2O3 thin films with thin SiO2 layers grown by in situ O3 oxidation. Journal of Applied Physics, 2004, 96, 2323-2329.	1.1	68

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19	Synthesis of SnS Thin Films by Atomic Layer Deposition at Low Temperatures. Chemistry of Materials, 2017, 29, 8100-8110.	3.2	68
20	Titanium dioxide thin films for next-generation memory devices. Journal of Materials Research, 2013, 28, 313-325.	1.2	67
21	Chemically Conformal ALD of SrTiO[sub 3] Thin Films Using Conventional Metallorganic Precursors. Journal of the Electrochemical Society, 2005, 152, C229.	1.3	66
22	Transformation of the Crystalline Structure of an ALD TiO[sub 2] Film on a Ru Electrode by O[sub 3] Pretreatment. Electrochemical and Solid-State Letters, 2006, 9, F5.	2.2	66
23	Precision Interface Engineering of an Atomic Layer in Bulk Bi₂Te₃ Alloys for High Thermoelectric Performance. ACS Nano, 2019, 13, 7146-7154.	7.3	66
24	Atomic Layer Deposition of ZrO2 Thin Films with High Dielectric Constant on TiN Substrates. Electrochemical and Solid-State Letters, 2008, 11, G9.	2.2	65
25	Growth Characteristics of Atomic Layer Deposited TiO[sub 2] Thin Films on Ru and Si Electrodes for Memory Capacitor Applications. Journal of the Electrochemical Society, 2005, 152, C552.	1.3	64
26	Growth and Characterization of Conducting ZnO Thin Films by Atomic Layer Deposition. Bulletin of the Korean Chemical Society, 2010, 31, 2503-2508.	1.0	64
27	Structure and Electrical Properties of Al-Doped HfO₂ and ZrO₂ Films Grown via Atomic Layer Deposition on Mo Electrodes. ACS Applied Materials & Interfaces, 2014, 6, 22474-22482.	4.0	63
28	Free-electron creation at the 60Â° twin boundary in Bi2Te3. Nature Communications, 2016, 7, 12449.	5.8	59
29	Improvement in the leakage current characteristic of metal-insulator-metal capacitor by adopting RuO2 film as bottom electrode. Applied Physics Letters, 2011, 99, .	1.5	58
30	Leaky Integrate-and-Fire Neuron Circuit Based on Floating-Gate Integrator. Frontiers in Neuroscience, 2016, 10, 212.	1.4	55
31	Oxygen-Vacancy-Induced Polar Behavior in (LaFeO3)2/(SrFeO3) Superlattices. Nano Letters, 2014, 14, 2694-2701.	4.5	53
32	Influence of the oxygen concentration of atomic-layer-deposited HfO2 films on the dielectric property and interface trap density. Applied Physics Letters, 2005, 86, 112907.	1.5	50
33	Role of Ru nano-dots embedded in TiO2 thin films for improving the resistive switching behavior. Applied Physics Letters, 2010, 97, .	1.5	49
34	Influences of metal, non-metal precursors, and substrates on atomic layer deposition processes for the growth of selected functional electronic materials. Coordination Chemistry Reviews, 2013, 257, 3154-3176.	9.5	48
35	High-Performance Thin-Film Transistors of Quaternary Indiumâ€“Zincâ€“Tin Oxide Films Grown by Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2019, 11, 14892-14901.	4.0	48
36	Nonâ€Volatile Control of 2DEG Conductivity at Oxide Interfaces. Advanced Materials, 2013, 25, 4612-4617.	11.1	47

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37	Impact of O3 feeding time on TiO2 films grown by atomic layer deposition for memory capacitor applications. Journal of Applied Physics, 2007, 102, 024109.	1.1	46
38	Plasma-Enhanced Atomic Layer Deposition of TiO[sub 2] and Al-Doped TiO[sub 2] Films Using N[sub 2]O and O[sub 2] Reactants. Journal of the Electrochemical Society, 2009, 156, G138.	1.3	46
39	Relation Between Enhancement in Growth and Thickness-Dependent Crystallization in ALD TiO[sub 2] Thin Films. Journal of the Electrochemical Society, 2011, 158, D6.	1.3	44
40	Atomic layer deposition of hafnium oxide from tert-butoxytris(ethylmethylamido)hafnium and ozone: rapid growth, high density and thermal stability. Journal of Materials Chemistry, 2008, 18, 4324.	6.7	43
41	Growth of RuO₂ Thin Films by Pulsed-Chemical Vapor Deposition Using RuO₄ Precursor and 5% H₂ Reduction Gas. Chemistry of Materials, 2010, 22, 5700-5706.	3.2	40
42	Reliability of neuronal information conveyed by unreliable neuristor-based leaky integrate-and-fire neurons: a model study. Scientific Reports, 2015, 5, 9776.	1.6	38
43	Highly sensitive flexible NO₂ sensor composed of vertically aligned 2D SnS₂ operating at room temperature. Journal of Materials Chemistry C, 2020, 8, 11874-11881.	2.7	38
44	Laser-irradiated inclined metal nanocolumns for selective, scalable, and room-temperature synthesis of plasmonic isotropic nanospheres. Journal of Materials Chemistry C, 2018, 6, 6038-6045.	2.7	37
45	Structurally and Electrically Uniform Deposition of High-k TiO[sub 2] Thin Films on a Ru Electrode in Three-Dimensional Contact Holes Using Atomic Layer Deposition. Electrochemical and Solid-State Letters, 2005, 8, F59.	2.2	35
46	SnO 2 thin films grown by atomic layer deposition using a novel Sn precursor. Applied Surface Science, 2014, 320, 188-194.	3.1	35
47	Catalytic activity for oxygen reduction reaction on platinum-based coreâ€“shell nanoparticles: all-electron density functional theory. Nanoscale, 2015, 7, 15830-15839.	2.8	34
48	Atomic Layer Deposition of TiO[sub 2] Films on Ru Buffered TiN Electrode for Capacitor Applications. Journal of the Electrochemical Society, 2009, 156, G71.	1.3	33
49	X-ray Irradiation Induced Reversible Resistance Change in Pt/TiO₂/Pt Cells. ACS Nano, 2014, 8, 1584-1589.	7.3	32
50	Chemical structures and electrical properties of atomic layer deposited HfO2 thin films grown at an extremely low temperature (â‰100Â°C) using O3 as an oxygen source. Applied Surface Science, 2014, 292, 852-856.	3.1	32
51	Evaluating the Top Electrode Material for Achieving an Equivalent Oxide Thickness Smaller than 0.4 nm from an Al-Doped TiO₂ Film. ACS Applied Materials & Interfaces, 2014, 6, 21632-21637.	4.0	31
52	Low-temperature wafer-scale synthesis of two-dimensional SnS₂. Nanoscale, 2018, 10, 17712-17721.	2.8	30
53	Permittivity Enhanced Atomic Layer Deposited HfO₂ Thin Films Manipulated by a Rutile TiO₂ Interlayer. Chemistry of Materials, 2010, 22, 4419-4425.	3.2	29
54	Design and Experimental Investigation of Thermoelectric Generators for Wearable Applications. Advanced Materials Technologies, 2017, 2, 1600292.	3.0	28

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55	Novel postâ€process for the passivation of a CMOS biosensor. Physica Status Solidi - Rapid Research Letters, 2008, 2, 4-6.	1.2	27
56	Growth of Noble Metal Ru Thin Films by Liquid Injection Atomic Layer Deposition. Journal of Physical Chemistry C, 2009, 113, 11329-11335.	1.5	26
57	Role of Interfacial Reaction in Atomic Layer Deposition of TiO₂ Thin Films Using Ti(O-<i>i</i>Pr)₂(tmhd)₂ on Ru or RuO₂ Substrates. Chemistry of Materials, 2011, 23, 976-983.	3.2	26
58	The mechanism for the suppression of leakage current in high dielectric TiO2 thin films by adopting ultra-thin HfO2 films for memory application. Journal of Applied Physics, 2011, 110, 024105.	1.1	26
59	Effect of spark plasma sintering conditions on the thermoelectric properties of (Bi0.25Sb0.75)2Te3 alloys. Journal of Alloys and Compounds, 2016, 678, 396-402.	2.8	25
60	Atomic layer deposition of HfO2 thin films using H2O2 as oxidant. Applied Surface Science, 2014, 301, 451-455.	3.1	24
61	Influence of the oxygen concentration of atomic-layer-deposited HfO2 gate dielectric films on the electron mobility of polycrystalline-Si gate transistors. Journal of Applied Physics, 2006, 99, 094501.	1.1	23
62	Liquid Injection Atomic Layer Deposition of Crystalline TiO[sub 2] Thin Films with a Smooth Morphology from Ti(O-i-Pr)[sub 2](DPM)[sub 2]. Journal of the Electrochemical Society, 2009, 156, D296.	1.3	23
63	Study on Initial Growth Behavior of RuO₂ Film Grown by Pulsed Chemical Vapor Deposition: Effects of Substrate and Reactant Feeding Time. Chemistry of Materials, 2012, 24, 1407-1414.	3.2	23
64	Enhancement of Mechanical Hardness in SnO_{<i>x</i>}N_{<i>y</i>} with a Dense High-Pressure Cubic Phase of SnO₂. Chemistry of Materials, 2016, 28, 7051-7057.	3.2	23
65	Impurity-free, mechanical doping for the reproducible fabrication of the reliable n-type Bi2Te3-based thermoelectric alloys. Acta Materialia, 2018, 150, 153-160.	3.8	23
66	Controlling the Al-Doping Profile and Accompanying Electrical Properties of Rutile-Phased TiO₂ Thin Films. ACS Applied Materials & Interfaces, 2014, 6, 7910-7917.	4.0	21
67	Impact of parasitic thermal effects on thermoelectric property measurements by Harman method. Review of Scientific Instruments, 2014, 85, 045108.	0.6	21
68	Control of the initial growth in atomic layer deposition of Pt films by surface pretreatment. Nanotechnology, 2015, 26, 304003.	1.3	21
69	Cation-Regulated Transformation for Continuous Two-Dimensional Tin Monosulfide. Chemistry of Materials, 2020, 32, 2313-2320.	3.2	21
70	<i>In situ</i> x-ray studies of oxygen surface exchange behavior in thin film La_{0.6}Sr_{0.4}Co_{0.2}Fe_{0.8}O_{3âˆ'Î´}. Applied Physics Letters, 2012, 101, 051603.	1.5	20
71	Wafer-Scale, Conformal, and Low-Temperature Synthesis of Layered Tin Disulfides for Emerging Nonplanar and Flexible Electronics. ACS Applied Materials & Interfaces, 2020, 12, 2679-2686.	4.0	20
72	Hardening of Biâ€“Te based alloys by dispersing B4C nanoparticles. Acta Materialia, 2015, 97, 68-74.	3.8	19

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73	Harman Measurements for Thermoelectric Materials and Modules under Non-Adiabatic Conditions. Scientific Reports, 2016, 6, 39131.	1.6	19
74	Interface Engineering for Extremely Large Grains in Explosively Crystallized TiO₂ Films Grown by Low-Temperature Atomic Layer Deposition. Chemistry of Materials, 2017, 29, 2046-2054.	3.2	19
75	Ta-Doped SnO₂ as a reductionâ€"resistant oxide electrode for DRAM capacitors. Journal of Materials Chemistry C, 2017, 5, 9405-9411.	2.7	19
76	Impact of Bimetal Electrodes on Dielectric Properties of TiO₂ and Al-Doped TiO₂ Films. ACS Applied Materials & Interfaces, 2012, 4, 4726-4730.	4.0	18
77	Chemistry of active oxygen in RuO_x and its influence on the atomic layer deposition of TiO₂ films. Journal of Materials Chemistry C, 2014, 2, 9993-10001.	2.7	18
78	Sn doping in thermoelectric Bi2Te3 films by metal-organic chemical vapor deposition. Applied Surface Science, 2015, 353, 232-237.	3.1	18
79	MoO₂ as a thermally stable oxide electrode for dynamic random-access memory capacitors. Journal of Materials Chemistry C, 2018, 6, 13250-13256.	2.7	18
80	Local Epitaxial Growth of Ru Thin Films by Atomic Layer Deposition at Low Temperature. Journal of the Electrochemical Society, 2011, 158, D477.	1.3	17
81	Atomic layer deposition of SnO2 thin films using tetraethyltin and H2O2. Ceramics International, 2019, 45, 20600-20605.	2.3	17
82	Multiprotocol-induced plasticity in artificial synapses. Nanoscale, 2014, 6, 15151-15160.	2.8	16
83	Fabrication and surface plasmon coupling studies on the dielectric/Ag structure for transparent conducting electrode applications. Optical Materials Express, 2014, 4, 2078.	1.6	16
84	High quality interfacial sulfur passivation via H₂S pre-deposition annealing for an atomic-layer-deposited HfO₂ film on a Ge substrate. Journal of Materials Chemistry C, 2016, 4, 850-856.	2.7	16
85	Controlling the Composition of Doped Materials by ALD: A Case Study for Al-Doped TiO[sub 2] Films. Electrochemical and Solid-State Letters, 2008, 11, G27.	2.2	15
86	High Growth Rate in Atomic Layer Deposition of TiO2 thin films by UV Irradiation. Electrochemical and Solid-State Letters, 2011, 14, H146.	2.2	14
87	Enhancement of Initial Growth of ZnO Films on Layer-Structured Bi₂Te₃ by Atomic Layer Deposition. Chemistry of Materials, 2014, 26, 6448-6453.	3.2	14
88	Atomic-Layer Deposition of Single-Crystalline BeO Epitaxially Grown on GaN Substrates. ACS Applied Materials & Interfaces, 2017, 9, 41973-41979.	4.0	14
89	Atomic-layer deposition of TiO2 thin films with a thermally stable (CpMe5)Ti(OMe)3 precursor. Applied Surface Science, 2021, 550, 149381.	3.1	14
90	Cross-linked structure of self-aligned p-type SnS nanoplates for highly sensitive NO₂ detection at room temperature. Journal of Materials Chemistry A, 2022, 10, 4711-4719.	5.2	14

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91	Effect of crystalline structure of TiO2 substrates on initial growth of atomic layer deposited Ru thin films. Applied Surface Science, 2011, 257, 4302-4305.	3.1	13
92	Strain-assisted, low-temperature synthesis of high-performance thermoelectric materials. Physical Chemistry Chemical Physics, 2014, 16, 3529.	1.3	13
93	Electric-field-induced Shift in the Threshold Voltage in LaAlO3/SrTiO3 Heterostructures. Scientific Reports, 2015, 5, 8023.	1.6	13
94	Improved interface properties of atomic-layer-deposited HfO2 film on InP using interface sulfur passivation with H2S pre-deposition annealing. Applied Surface Science, 2015, 357, 2306-2312.	3.1	13
95	Growth and Characterization of BeO Thin Films Grown by Atomic Layer Deposition Using H₂O and O₃ as Oxygen Sources. Journal of Physical Chemistry C, 2017, 121, 17498-17504.	1.5	13
96	Strategic Selection of the Oxygen Source for Low Temperatureâ€Atomic Layer Deposition of Al₂O₃ Thin Film. Advanced Electronic Materials, 2019, 5, 1800680.	2.6	13
97	Atomic layer deposited HfO2 and HfO2/TiO2 bi-layer films using a heteroleptic Hf-precursor for logic and memory applications. Journal of Materials Chemistry, 2011, 21, 18497.	6.7	12
98	Thickness-Dependent Electrocaloric Effect in Pb0.9La0.1Zr0.65Ti0.35O3 Films Grown by Solâ€“Gel Process. Journal of Electronic Materials, 2016, 45, 1057-1064.	1.0	12
99	Texture-induced reduction in electrical resistivity of p-type (Bi,Sb)2Te3 by a hot extrusion. Journal of Alloys and Compounds, 2018, 764, 261-266.	2.8	12
100	Domain epitaxy of crystalline BeO films on GaN and ZnO substrates. Journal of the American Ceramic Society, 2019, 102, 3745-3752.	1.9	12
101	Electrical properties of high-k HfO2 films on Si1âˆ’xGex substrates. Microelectronic Engineering, 2005, 80, 222-225.	1.1	11
102	Dynamic temperature response of electrocaloric multilayer capacitors. Applied Physics Letters, 2014, 104, .	1.5	11
103	Correction of the Electrical and Thermal Extrinsic Effects in Thermoelectric Measurements by the Harman Method. Scientific Reports, 2016, 6, 26507.	1.6	11
104	Atomic layer deposition of Ta-doped SnO2 films with enhanced dopant distribution for thermally stable capacitor electrode applications. Applied Surface Science, 2019, 497, 143804.	3.1	11
105	Combined hot extrusion and spark plasma sintering method for producing highly textured thermoelectric Bi2Te3 alloys. Journal of the European Ceramic Society, 2020, 40, 3042-3048.	2.8	11
106	Enhanced thermal stability of Bi2Te3-based alloys via interface engineering with atomic layer deposition. Journal of the European Ceramic Society, 2020, 40, 3592-3599.	2.8	11
107	Modular instrument mounting system for variable environment in operando X-ray experiments. Review of Scientific Instruments, 2013, 84, 025111.	0.6	10
108	Asymmetry in electrical properties of Alâ€doped TiO₂ film with respect to bias voltage. Physica Status Solidi - Rapid Research Letters, 2015, 9, 410-413.	1.2	10

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109	Giant Electroresistive Ferroelectric Diode on 2DEG. Scientific Reports, 2015, 5, 10548.	1.6	10
110	Advanced Silicon-on-Insulator: Crystalline Silicon on Atomic Layer Deposited Beryllium Oxide. Scientific Reports, 2017, 7, 13205.	1.6	10
111	Carrier Modulation in Bi2Te3-Based Alloys via Interfacial Doping with Atomic Layer Deposition. Coatings, 2020, 10, 572.	1.2	10
112	Atomic layer deposition of TiO₂ and Alâ€doped TiO₂ films on Ir substrates for ultralow leakage currents. Physica Status Solidi - Rapid Research Letters, 2011, 5, 262-264.	1.2	9
113	Thermopower Enhancement of Bi2Te3 Films by Doping I Ions. Journal of Electronic Materials, 2014, 43, 2000-2005.	1.0	9
114	Orientation-Controlled Growth of Pt Films on SrTiO₃ (001) by Atomic Layer Deposition. Chemistry of Materials, 2015, 27, 6779-6783.	3.2	9
115	Polarity-tunable spin transport in all-oxide multiferroic tunnel junctions. Nanoscale, 2016, 8, 10799-10805.	2.8	9
116	Correct extraction of frequency dispersion in accumulation capacitance in InGaAs metal-insulator-semiconductor devices. Electronic Materials Letters, 2016, 12, 768-772.	1.0	9
117	Substrate Surface Modification for Enlarging Two-Dimensional SnS Grains at Low Temperatures. Chemistry of Materials, 2020, 32, 9026-9033.	3.2	9
118	3D architectures of single-crystalline complex oxides. Materials Horizons, 2020, 7, 1552-1557.	6.4	9
119	Capacitanceâ€“voltage analysis of LaAlO3/SrTiO3 heterostructures. Applied Physics Letters, 2013, 102, 112906.	1.5	8
120	Atomic engineering of metastable BeO6 octahedra in a rocksalt framework. Applied Surface Science, 2020, 501, 144280.	3.1	8
121	Mass-Production Memories (DRAM and Flash). , 2014, , 73-122.		8
122	Defect-Controlled, Scalable Layer-by-Layer Assembly of High-k Perovskite Oxide Nanosheets for All Two-Dimensional Nanoelectronics. Chemistry of Materials, 2021, 33, 8685-8692.	3.2	8
123	Control of conducting filaments in TiO2 films by a thin interfacial conducting oxide layer at the cathode. Applied Physics Letters, 2013, 102, 082903.	1.5	7
124	High mobility, large linear magnetoresistance, and quantum transport phenomena in Bi₂Te₃films grown by metallo-organic chemical vapor deposition (MOCVD). Nanoscale, 2015, 7, 17359-17365.	2.8	7
125	Growth Enhancement and Nitrogen Loss in ZnO_{<i>x</i>}N_{<i>y</i>} Low-Temperature Atomic Layer Deposition with NH₃. Journal of Physical Chemistry C, 2015, 119, 23470-23477.	1.5	7
126	Resistive Switching of Ta2O5-Based Self-Rectifying Vertical-Type Resistive Switching Memory. Journal of Electronic Materials, 2018, 47, 162-166.	1.0	7

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127	Mapping thermoelectric properties of polycrystalline n-type Bi2Te3-xSex alloys by composition and doping level. Journal of Alloys and Compounds, 2020, 844, 155828.	2.8	7
128	Towards spin-polarized two-dimensional electron gas at a surface of an antiferromagnetic insulating oxide. Physical Review B, 2016, 94, .	1.1	6
129	A two-step synthesis process of thermoelectric alloys for the separate control of carrier density and mobility. Journal of Alloys and Compounds, 2017, 727, 191-195.	2.8	6
130	Triboelectric charge generation by semiconducting SnO2 film grown by atomic layer deposition. Electronic Materials Letters, 2017, 13, 318-323.	1.0	6
131	Wall-thickness-dependent strength of nanotubular ZnO. Scientific Reports, 2017, 7, 4327.	1.6	6
132	A novel class of oxynitrides stabilized by nitrogen dimer formation. Scientific Reports, 2018, 8, 14471.	1.6	6
133	Domain engineering of epitaxial (001) Bi2Te3 thin films by miscut GaAs substrate. Acta Materialia, 2020, 197, 309-315.	3.8	6
134	Enhancement of electrical performance of atomic layer deposited SnO films <i>via</i> substrate surface engineering. Journal of Materials Chemistry C, 2021, 9, 12314-12321.	2.7	6
135	Nonvolatile Resistance Switching on Two-Dimensional Electron Gas. ACS Applied Materials & Interfaces, 2014, 6, 17785-17791.	4.0	5
136	Suppression of bulk conductivity and large phase relaxation length in topological insulator Bi2-Î´SnÎ´Te3 epitaxial thin films grown by Metal-Organic Chemical Vapor Deposition (MOCVD). Journal of Alloys and Compounds, 2017, 723, 942-947.	2.8	5
137	Confined polaronic transport in (LaFeO3)<i>n</i>/(SrFeO3)1 superlattices. APL Materials, 2019, 7, .	2.2	5
138	Stepwise growth of crystalline MoS₂ in atomic layer deposition. Journal of Materials Chemistry C, 2022, 10, 7031-7038.	2.7	5
139	Thermal stress-assisted annealing to improve the crystalline quality of an epitaxial YSZ buffer layer on Si. Journal of Materials Chemistry C, 2022, 10, 10027-10036.	2.7	5
140	Thermoelectric Properties of Highly Deformed and Subsequently Annealed p-Type (Bi0.25Sb0.75)2Te3 Alloys. Journal of Electronic Materials, 2014, 43, 1726-1732.	1.0	4
141	Bio-fabrication of nanomesh channels of single-walled carbon nanotubes for locally gated field-effect transistors. Nanotechnology, 2017, 28, 025304.	1.3	4
142	A Ruâ€“Pt alloy electrode to suppress leakage currents of dynamic random-access memory capacitors. Nanotechnology, 2018, 29, 455202.	1.3	4
143	Crystal properties of atomic-layer deposited beryllium oxide on crystal and amorphous substrates. Semiconductor Science and Technology, 2019, 34, 115021.	1.0	4
144	Effect of Mechanical Deformation on Thermoelectric Properties of p-Type(Bi0.225Sb0.775)2Te3Alloys. Journal of Nanomaterials, 2013, 2013, 1-6.	1.5	3

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145	A differential method for measuring cooling performance of a thermoelectric module. Applied Thermal Engineering, 2015, 87, 209-213.	3.0	3
146	Thermoelectric Properties of Sn-Doped Bi0.4Sb1.6Te3 Thin Films. Journal of Electronic Materials, 2015, 44, 1573-1578.	1.0	3
147	Investigation of phases and chemical states of tin titanate films grown by atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 012404.	0.9	3
148	Atomically thin indium oxide transistors. Nature Electronics, 2022, 5, 129-130.	13.1	3
149	Electrically Benign Ru Wet Etching Method for Fabricating Ruâ^•TiO[sub 2]â^•Ru Capacitor. Journal of the Electrochemical Society, 2011, 158, G47.	1.3	2
150	Hot rolling process for texture development and grain refinement of n-type Bi2Te3 alloys. Materials Letters, 2021, 301, 130278.	1.3	2
151	Effects of oxygen sources on properties of atomic-layer-deposited ferroelectric hafnium zirconium oxide thin films. Ceramics International, 2022, 48, 3280-3286.	2.3	2
152	Oxidation of thermoelectric Bi2Te3-based alloys by atomic layer deposition of Ru metal. Materials Letters, 2022, 320, 132321.	1.3	2
153	Fabrication of a metal-oxide-semiconductor-type capacitive microtip array using SiO2 or HfO2 gate insulators. Applied Physics Letters, 2004, 85, 5412-5414.	1.5	1
154	Atomic Layer Deposition of Ru Thin Films Using 2,4-(dimethylpentadienyl)(ethylcyclopentadienyl) Ru by a Liquid Injection System. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	1
155	Impedance-based interfacial analysis of the LaAlO3/SrTiO3 oxide heterostructure involving a 2-dimensional electron gas layer. Journal of Physics and Chemistry of Solids, 2015, 82, 60-66.	1.9	1
156	Characteristics of a Capacitive Probe Array for Direct Surface Charge Detection. Electrochemical and Solid-State Letters, 2007, 10, H34.	2.2	0
157	Impedance-based interpretations in 2-dimensional electron gas conduction formed in the LaAlO 3 /Sr x Ca 1â^'x TiO 3 /SrTiO 3 system. Journal of Physics and Chemistry of Solids, 2016, 93, 131-136.	1.9	0
158	Engineering of AlON interlayer in Al 2 O 3 /AlON/In 0.53 Ga 0.47 As gate stacks by thermal atomic layer deposition. Current Applied Physics, 2018, 18, 919-923.	1.1	0
159	Smart forensic kit: Real-time estimation of postmortem interval using a highly sensitive gas sensor for microbial forensics. Sensors and Actuators B: Chemical, 2020, 322, 128612.	4.0	0